

Fabrication of Highly Sensitive Flexible Phototransistors through Unidirectional Floating Film Transfer Method Using P4T2F-HD Thin Film

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Supplementary Information SI-1

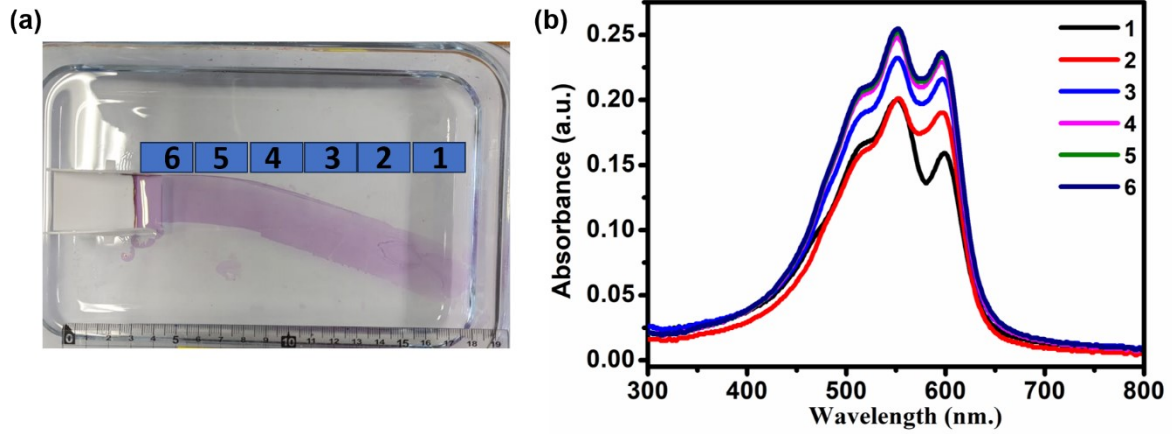


Figure S1: (a) represents the UFTM thin film with the no of samples fabricated from the film (b) represents the UV-spectrum of different samples from the UFTM thin film

Supplementary Information SI-2

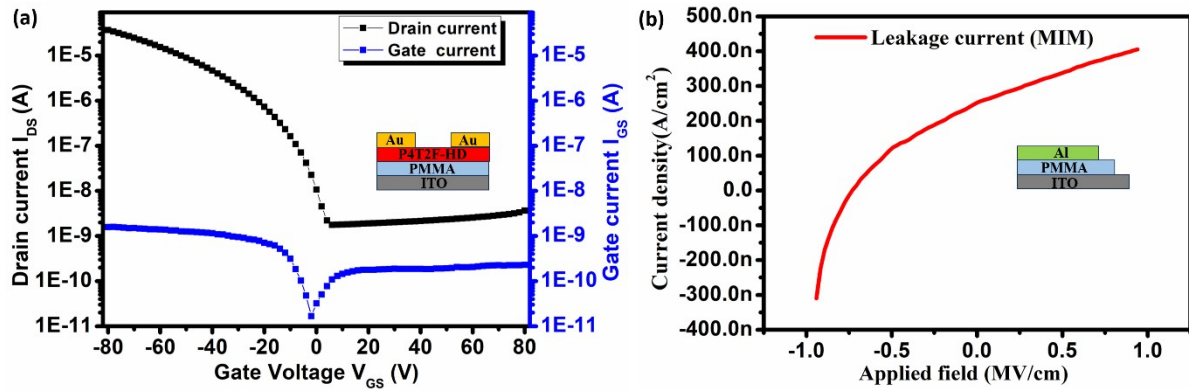


Figure S2: (a) Represents the gate current from the TFT along with drain current (b) leakage current from the MIM structure.

Supplementary Information SI-3

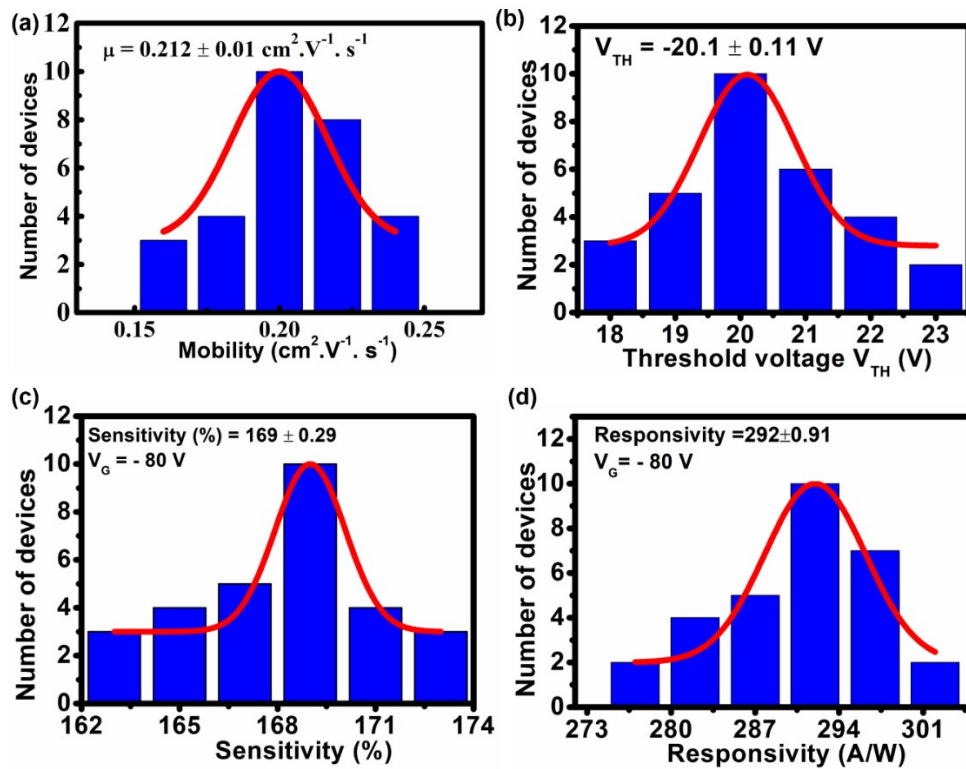


Figure S3: represents the static data of (a) mobility v/s devices fabricated in different batches, (b) threshold voltage of different devices, (c) sensitivity of devices at -80V at intensity of 125 $\mu\text{W}/\text{cm}^2$ (d) responsivity of devices at -80V at intensity of 125 $\mu\text{W}/\text{cm}^2$.

Supplementary Information SI-4

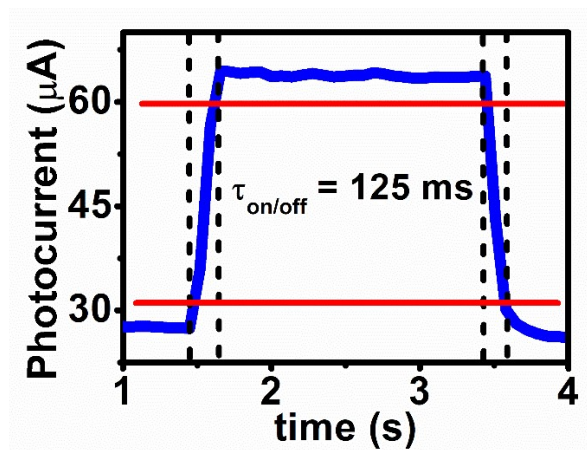


Figure S4: represents the on/off switching of OPTs.